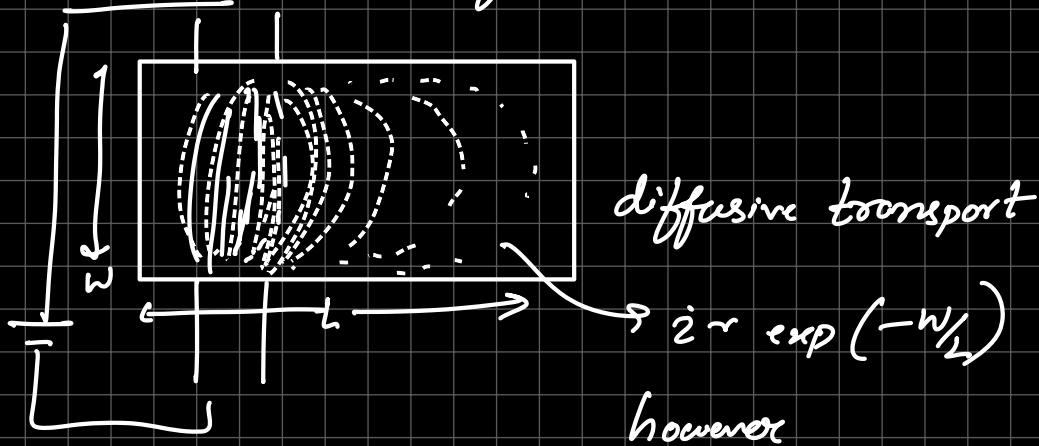


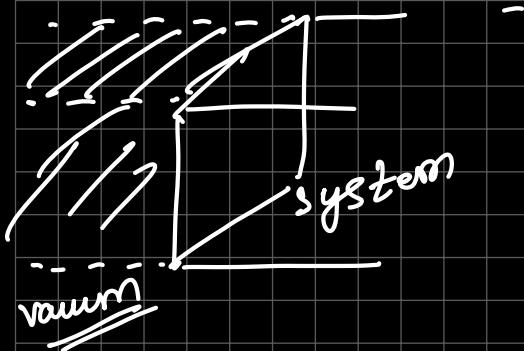
(dec 23 in MD)

some decay of the CdTe-HgTe heterostructure



3 dim Dirac eqn

$$\partial H_{3D} = v p_y \tau \gamma + v \beta_2 \alpha_2 - B(p_y^2 + p_z^2) \beta$$



$$H_{\text{eff}} = \left[\langle \psi_1 |, \langle \psi_2 | \right] \partial H_{3D} \left[| \psi_1 \rangle, | \psi_2 \rangle \right]^T$$

$$\psi_1 = \begin{pmatrix} \text{sgn} \\ 0 \\ 0 \\ 0 \end{pmatrix} \left(e^{-\frac{\gamma}{\epsilon_+}} - e^{-\frac{\gamma}{\epsilon_-}} \right) e^{i(k_y y + k_z z)}$$

$$\psi_2 = \begin{pmatrix} 0 \\ \text{sgn } B \\ 0 \\ 0 \end{pmatrix} \left(e^{-\frac{\gamma}{\epsilon_+}} - e^{-\frac{\gamma}{\epsilon_-}} \right) e^{i(k_y y + k_z z)}$$

$$\langle \psi_1 | \partial H_{\text{eff}} | \psi_1 \rangle = v p_y \text{sgn}(B) \sigma_2 \xrightarrow{\text{from}} \sigma_y$$

$$\langle \psi_1 | \alpha_2 | \psi_1 \rangle = \langle \psi_1 | \begin{pmatrix} 0 & \sigma_2 \\ \sigma_2 & 0 \end{pmatrix} \begin{pmatrix} \text{sgn } B \\ 0 \\ 0 \\ 0 \end{pmatrix} \rangle = \langle \psi_1 | \begin{pmatrix} 0 \\ -2 \\ \text{sgn } B \\ 0 \end{pmatrix} \rangle = 0$$

$$\text{But } \langle \psi_2 | \alpha_2 | \psi_1 \rangle = \begin{pmatrix} 0 & \text{sgn } B & -2 & 0 \end{pmatrix} \begin{pmatrix} 0 \\ -2 \\ \text{sgn } B \\ 0 \end{pmatrix} = -2i \text{sgn } B$$

$$\therefore \langle \psi_2 | \nu p_z \alpha_2 | \psi_1 \rangle = -2\nu P_z \operatorname{sgn} B ;$$

$$\therefore (\nu p_z \alpha_2)_{2x2} = \begin{pmatrix} 0 & +i \\ -i & 0 \end{pmatrix} \nu P_z \operatorname{sgn} B = -\nu \underline{\underline{P_z \operatorname{sgn} B}} \sigma_y$$

(ignoring 2)

$$\therefore \Delta E = \nu p_y \operatorname{sgn} B \sigma_2 - \nu p_z \operatorname{sgn} B \sigma_y = \nu \operatorname{sgn} B (p_y \sigma_2 - p_z \sigma_y) \\ = \nu \operatorname{sgn} B (\vec{p}_x \vec{\sigma})_z$$

But now we define

$$|\psi_1\rangle = \frac{1}{\sqrt{2}} (|\psi_1\rangle - i|\psi_2\rangle)$$

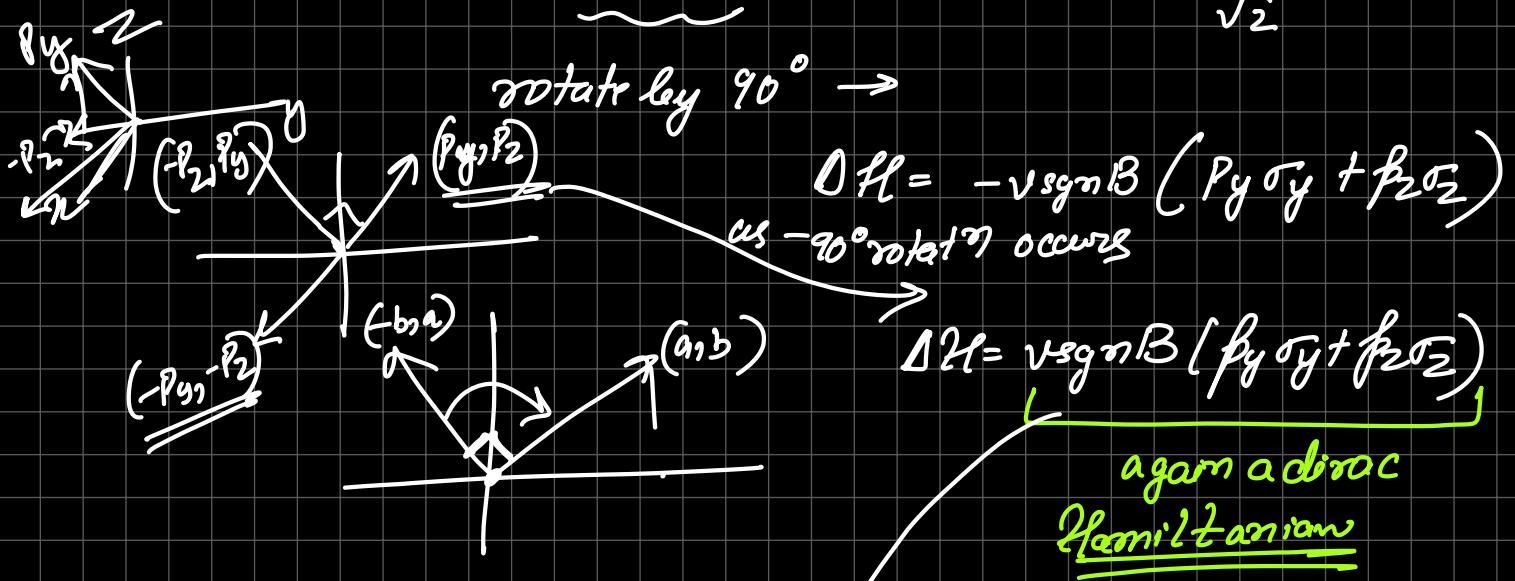
$$|\psi_2\rangle = \frac{-i}{\sqrt{2}} (|\psi_1\rangle + i|\psi_2\rangle)$$

$$\text{or } \begin{pmatrix} \psi_1 \\ \psi_2 \end{pmatrix} = \frac{1}{\sqrt{2}} \underbrace{\begin{pmatrix} 1 & -i \\ -i & +1 \end{pmatrix}}_{M} \begin{pmatrix} |\psi_1\rangle \\ |\psi_2\rangle \end{pmatrix} \Rightarrow \overline{\Psi} = M \overline{\Psi}$$

$$\Delta E (\phi_1, \phi_2 \text{ basis}) = \overline{\Psi}^T \text{off } \overline{\Psi} = 2 \overline{\Psi}^T \text{mat} \text{ mat}^T \overline{\Psi}$$

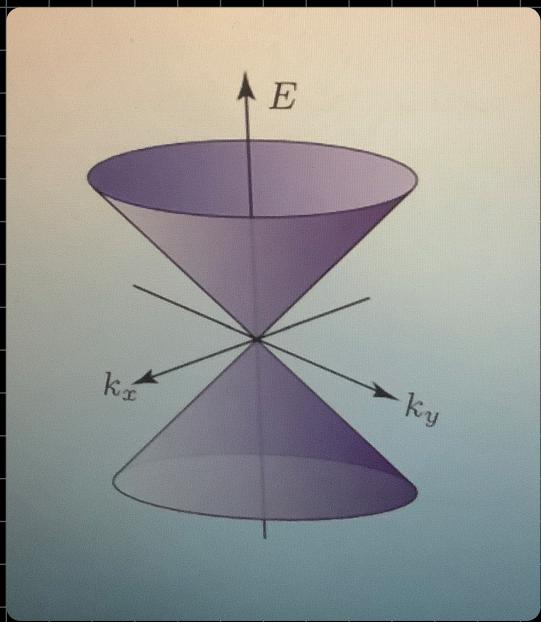
$$\therefore \text{off} \rightarrow \underbrace{m \Delta E \text{ mat}^T}$$

$$\text{but } m = \frac{1-i\sigma_x}{\sqrt{2}} = e^{-i\frac{\sigma_x}{2}}$$



$\epsilon_{\pm} = \pm vP$, $P = \sqrt{p_x^2 + p_z^2} \Rightarrow$ "Dirac like disp., but for a propagating boundary mode"

We get a "Dirac Cone" but for surface states



Note:-

- ① σ_i are not "real" spin components
- ② exact solution

where

$$\psi_+^0 = \begin{pmatrix} I \\ \cos \frac{\theta}{2} \operatorname{sgn}(B) \\ -i \sin \frac{\theta}{2} \operatorname{sgn}(B) \\ \sin \frac{\theta}{2} \\ i \cos \frac{\theta}{2} \end{pmatrix} \quad (2.61)$$

and

$$\psi_-^0 = \begin{pmatrix} \sin \frac{\theta}{2} \operatorname{sgn}(B) \\ i \cos \frac{\theta}{2} \operatorname{sgn}(B) \\ -\cos \frac{\theta}{2} \\ i \sin \frac{\theta}{2} \end{pmatrix} \quad (2.62)$$

with the dispersion relation $\epsilon_{p,\pm} = \pm vp \operatorname{sgn}(B)$. $\tan \theta = p_y / p_z$. The penetration depth becomes p dependent,

$$\xi_{\pm}^{-1} = \frac{v}{2|B|\hbar} \left(1 \pm \sqrt{1 - 4mB + 4B^2p^2/\hbar^2} \right). \quad (2.63)$$

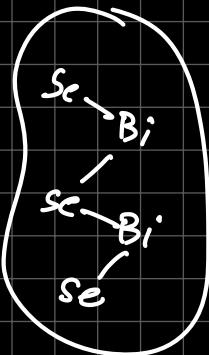
Gapless propagating edge modes
"Dirac like Hamiltonian"
for surface

Topological Insulators & Expt relevance

Real material: Bi_2Se_3 — Quintuple layer



Only p_z orbitals matter



→ people looked in 3d where a similar "Band inversion" happens. For e.g. Alloys Pb_xSn_{1-x} → x can be tuned to go into int. band situation

$\swarrow \quad \searrow$

$x=0$, one type of symmetry of bonds $x=1$, other type of bonds

→ 3d materials (alloys can be used to tune the bond)

↳ as function of x , it has band inversion

$\swarrow \quad \searrow$

bulk = insulator surface = gapless modes

⇒ Bi_2Se_3 → among the 1st materials to be scanned

↳ by ARPES → shine light on the crystal at a fixed relative angle & look at

Allows you to map bandstructure ← [the outgoing electron
 ↓ can detect its \vec{k} & Energy of it.
 measure "filled states"

→ Bi_2Se_3 → known to be SC for a lot of time

↳ but inside the gap, \exists a few states (edge states)

↳ "they saw cones touching each other"

↳ $0 \sim 50$ meV where it's valid.

dispersion of surface state looks

like $E_F \sim (\epsilon_x P_x + \epsilon_y P_y)$ [as our calc]

Diff from graphene ⇒ no info about spin

→ but here the $E_{\text{surface}}^{\text{eff}}$ has info

about spin of the electrons.

spin is coupled to momenta → spin resolved photoemission spectroscopy

congive info about spin resolved bondstructure.

⇒ (in real materials) even/odd # of dirac cones.

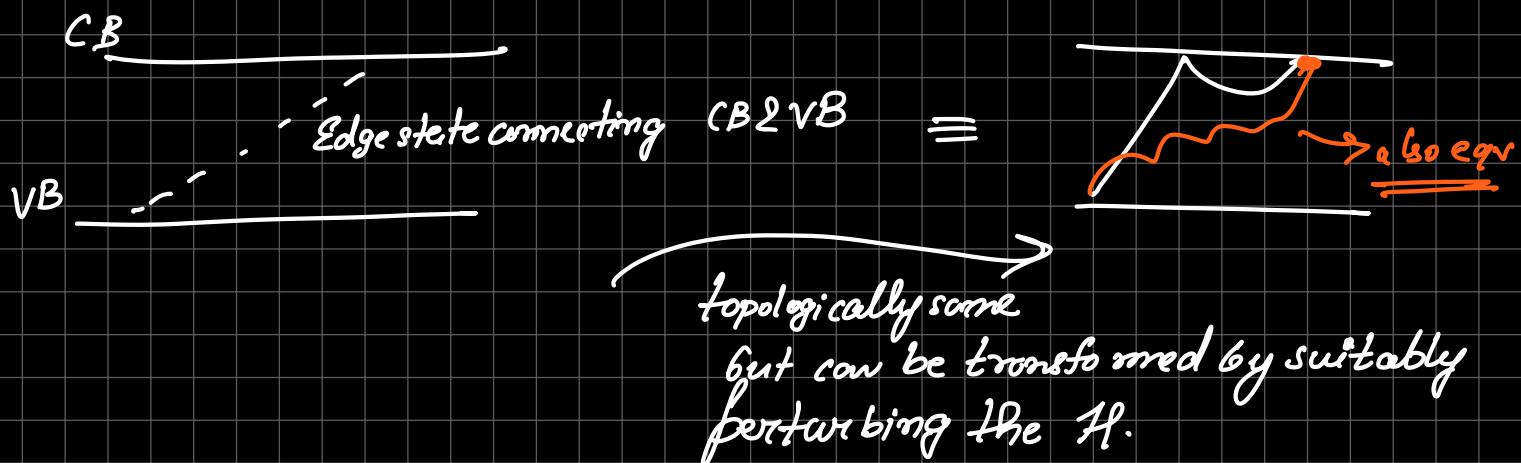
for even, it's
not a strong topological
insulator as even #

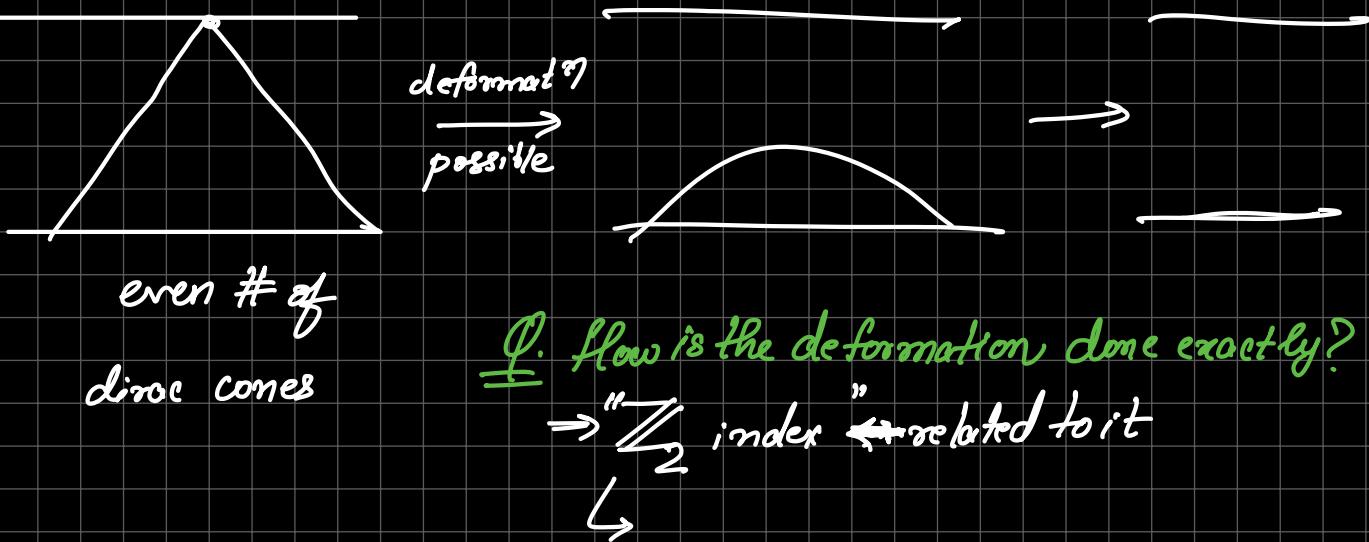
Can be roughly equated to

having no cones in
Bandstructure.

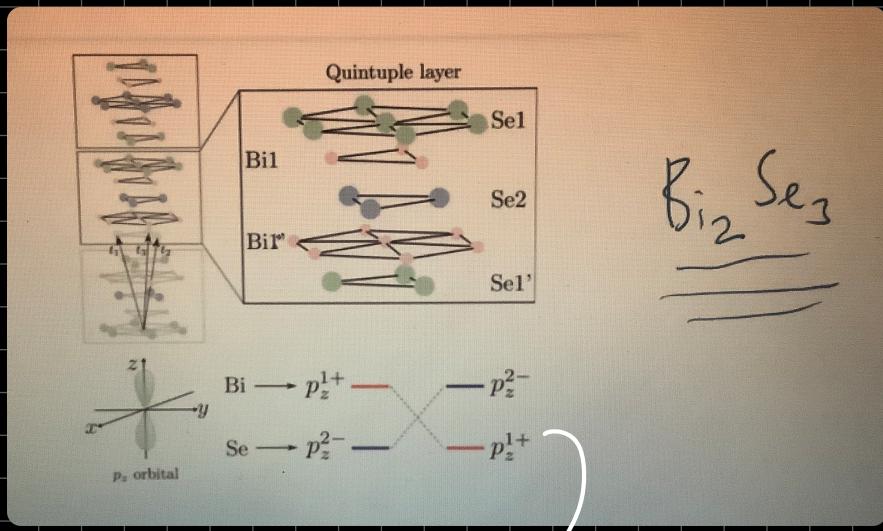
→ odd
→ strong topo. insulator
→ cannot make the
dirac cones disappear

Check:- Vanderbilt's book for
a discussion of the invariance
of topological systems.





Bi_2Se_3 :-



Coupling b/w ~~gas~~
Principle layers is
vdw (weak) but
interlayer is strong

have "partially filled" P_z orbitals → jump for what happens
↓
close to form energy.

"inversion symmetry present"

- Basis:- Close to fermi energy

$$|P_z^1+, \uparrow\rangle, |P_z^2+, \downarrow\rangle, |P_z^{2-}, \uparrow\rangle, |P_z^{2-}, \downarrow\rangle$$

$\text{Bi}_2\text{Se} \rightarrow$ large Z_{eff} , so large SOC & hence (probably spin polarized)
spin attributed basis is chosen.

The effective hamiltonian

$$H = \mathcal{E}(p) + \sum_{i=1,2,3} v_i p_i \alpha_i + (M - \sum B p_i^2) \beta$$

$$\mathcal{E}(p) = -D_{\parallel} (\cancel{p_x^2 + p_y^2}) - D_{\perp} \cancel{p_z^2}$$

\rightarrow Heuristics \rightarrow • A gen decomp into α_i, β is ofc possible, H being 4x4

• now wkt TRS is present, we apply $\vec{k} \cdot \vec{p}$

\Downarrow

$$\alpha_i \xrightarrow{\text{TRS}} -\alpha_i$$

$$\beta \xrightarrow{\text{TRS}} \beta \quad \begin{matrix} \hookrightarrow \text{pair with odd terms in} \\ \text{momentum.} \end{matrix}$$

in p_x, p_y \hookrightarrow pair with even terms of β
 you'll get $\epsilon^{(n)} + \frac{p^2}{2m}$ \hookrightarrow pair with odd terms of β
 terms like $\epsilon^{(n)}$ \downarrow demand $f^{(n)}$ be odd under TRS
 gives rise to type terms $\propto p_i \alpha_i$ \downarrow give rise to βp^2 terms of H .

[side note: Hone & male \rightarrow Gaps out Graphene & introduces SOC]
 \hookrightarrow ribbon geo was done in lecture]

\rightarrow @ Shoucheng Zhang \Rightarrow used fcc Te - ColTe \rightarrow bonds, inverted
 "at the edges, the mode is topological"

→ Graphene (weak SOC) when put on an insulator (strong SOC)

can be approximated to have a strong SOC.

probably

hole &
hole can be
realized on it
but Bi_2Se_3 also generates
~~an even model.~~